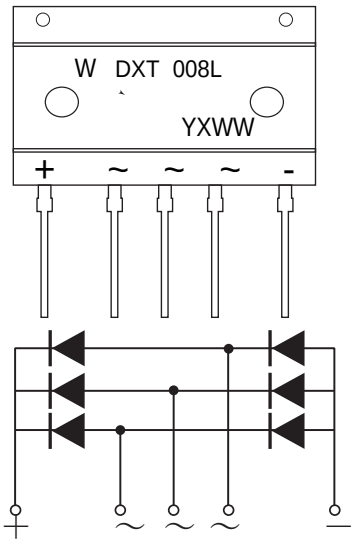
DXT6008L

23-NOV-2021

Low VF Three-phase Bridge Rectifiers



) H D W X U H V

- Glass Passivated Chip Junction
- Low IRRM
- Low VF
- High VRRM
- Special frame design for heat dissipation

% H Q H I L W V

- Case: DXT
- Terminals: Solderable Per MIL-STD-750
- Reduced power loss and switching transistor

3 D U D P H W H U	Symbols	DXT**6008L**	8 Q L W V
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	800	V
Maximum RMS voltage	V_{RMS}	560	V
Maximum DC Blocking Voltage	V_{DC}	800	V
Average Rectified Output Current	I_o	60	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	450	A
I^2t rating for fusing (1ms< t < 10ms)	I^2t	840	A^2S
Type Forward Voltage at 30.0A	V_F	0.93	V
Maximum Forward Voltage at 30.0 A			
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	I_R	10 500	μA
Typical Junction Capacitance Note1	C_j	50	pF
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +1	°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.
2. Mounted on glass epoxy PC board with 4×1.5"×1.5"（3.81×3.81 cm）copper pad.

RATINGS AND CHARACTERISTICS CURVES (TA = 25 ˚C unless otherwise noted)

Figure 1. Derating Curve